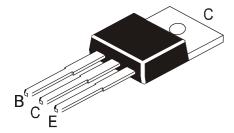


NPN SILICON PLANAR POWER TRANSISTOR

BU508AT

TO-220 Plastic Package



High Voltage, High-Speed Switching Transistor Intended for use in Horizontal Deflection Circuits of Colour Televisions

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT V V A	
Collector Emitter Voltage	V _{CES}	1500		
Collector Emitter Voltage	V _{CEO}	700		
Collector Current (DC)	I _C	8		
Collector Current (Peak)	I _{CM}	15	A	
Base Current (DC)	I _B	4	A	
Base Current (Peak)	I _{BM}	6	A	
Reverse Base Current (DC or average over any 20 ms period)	-I _{B(AV)}	100	mA	
Reverse Base Current (Peak Value)	*-I _{BM}	5	A	
Power Dissipation upto T _c =25 ^o C	P _{tot}	60	W	
Operating and Storage Junction Temperature Range	T _{j,} T _{stg}	- 65 to +150	°C	

*Turn off Current

ELECTRICAL CHARACTERISTICS (T_c=25°C unless specified otherwise)

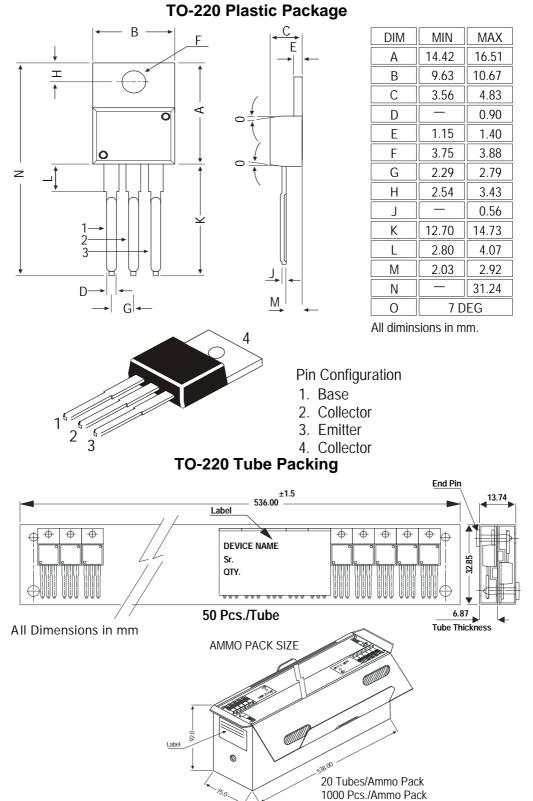
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector Cut off Current	**I _{CES}	V _{CE} =V _{CES} max, V _{BE} =0			1.0	mA
		T _j =125⁰C				
		V _{CE} =V _{CES} max, V _{BE} =0			2.0	mA
Emitter Cut off Current	I _{EBO}	$V_{EB}=6V, I_{C}=0$			10	mA
Collector Emitter Sustaining Voltage	*V _{CEO(sus)}	I _C =100mA, I _B =0, L=25mH	700			V
DC Current Gain	*h _{FE}	I _C =4.5A, V _{CE} =5V	2.25			
Collector Emitter Saturation Voltage	*V _{CE(sat)}	I _C =4.5A, I _B =2A			1.0	V
Base Emitter Saturation Voltage	*V _{BE(sat)}	I _C =4.5A, I _B =2A			1.3	V
Transition Frequency	f _T	I _C =0.1A, V _{CE} =5V, f=5MHz		7		MHz
Collector Capacitance	C _C	I _E =ie=0, V _{CB} =10V, f=1MHz		125		рF

**Measured with half-sinewave Voltage (curve tracer)

*Pulse Test: Pulse Width=5ms, Duty Cycle<10%

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Packing Detail

PACKAGE	STANDARDPACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-220 /FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1.0K	17" x 15" x 13.5"	16.0K	36 kgs
	50 pcs/tube	120 gm/50 pcs	3.5" x 3.7" x 21.5"	1.0K	19" x 19" x 19"	10.0K	29 kgs

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Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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